

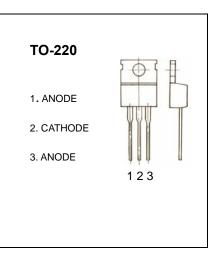
SHENZHEN CITY KOO CHIN ELECTRONICS LIMITED

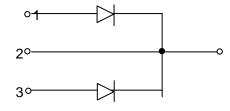
MBR1030CT-MBR1060CT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- · Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- · Low Power Loss, High Efficiency
- · High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- \cdot For Use in Low Voltage, High Frequency Inverters, Free
- Wheeling, and Polarity Protection Applications





ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Characteristic	Symbol	MBR 1030CT	MBR 1035CT	MBR 1040CT	MBR 1045CT	MBR 1050CT	MBR 1060CT	Unit
Peak Repetitive Reverse Voltage	V _{RRM}							
Working Peak Reverse Voltage	V _{RWM}	30	35	40	45	50	60	V
DC Blocking Voltage	V _R							
RMS Reverse Voltage	V _{R(RMS)}	21	24.5	28	31.5	35	42	V
Average Rectified Output Current	I _O 10						А	
(Note 1) @ T _c =105℃	10	10						A
Non-Repetitive Peak Forward Surge Current								
8.3ms Single half sine-wave superimposed on	I _{FSM}	125						А
rated load (JEDEC Method)								
Repetitive Peak Reverse Surge Current	I _{RRM}	1.0					А	
@ t≤ 2.0µs	I.U						A	
Forward Voltage Drop @ I⊧=5.0A, Tc=125℃		0.57 0.70 0.70 0.80					70	v
@ I _F =5.0A, T _C = 25℃	V _{FM}						80	
@ I _F =10A, T _C = 25℃		0.84				0.	0.95	
Peak Reverse Current @ T _C = 25℃	I _{RM}	0.1						mA
at Rated DC Blocking Voltage @ T _c =125℃	IRM	15						
Typical Junction Capacitance (Note 2)	Cj	150						pF
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150					°C	

Notes: 1. Thermal resistance junction to case mounted heat sink.

2. Measured at 1.OMHz and applied reverse voltage of 4.0V DC.

Typical Characteristics

MBR1030CT-1060CT

